

1. Global joint venture starts operations as WeEn Semiconductors

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Thank you for your cooperation and understanding,

WeEn Semiconductors



Product data sheet

1. General description

High voltage, high speed, planar passivated NPN power switching transistor in a SOT54 (TO92) plastic package intended for use in low power SMPS emitter switching circuits.

2. Features and benefits

- Fast switching
- · High base current drive capability
- High voltage capability
- · Very low switching and conduction losses

3. Applications

- · Emitter-switched low power SMPS circuits
- Self Oscillating Power Supplies
- · AC-DC converters
- DC-AC inverters

4. Pinning information

Table 1. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		С
2	С	collector		В
3	В	base	() () () 	B Th
			321 TO-92 (SOT54)	sym123

5. Ordering information

Table 2. Ordering information

Type number	Package				
	Name	Description	Version		
TB100	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54		

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6. Marking

Table 3. Marking codes

Type number	Marking code
TB100	TB100

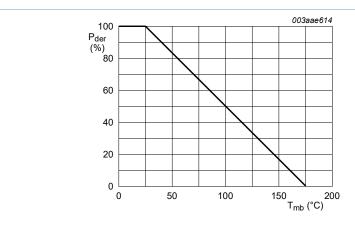
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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	700	V
V_{CBO}	collector-base voltage	I _E = 0 A	-	700	V
Ic	collector current	DC	-	1	Α
I _{CM}	peak collector current		-	2	Α
I_{B}	base current		-	0.5	Α
I _{BM}	peak base current		-	3	Α
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 1</u>	-	2	W
T_{stg}	storage temperature		-65	150	°C
T_j	junction temperature		-	150	°C



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

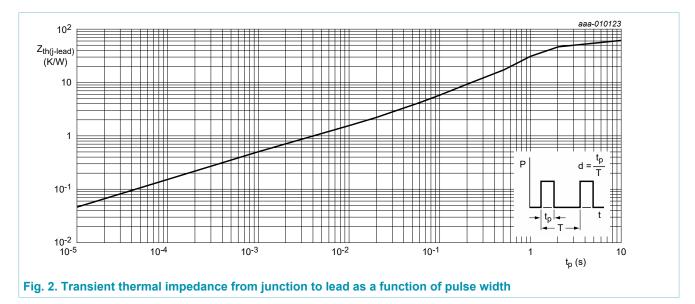
Fig. 1. Normalized total power dissipation as a function of mounting base temperature

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead		-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted; lead length = 4 mm; Fig. 2	-	150	-	K/W



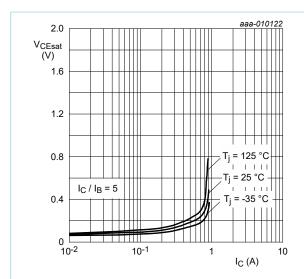
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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					,
I _{CES}	collector-emitter cut-off	V _{BE} = 0 V; V _{CE} = 700 V	-	8.0	100	μA
	current (base shorted)	V _{BE} = 0 V; V _{CE} = 700 V; T _j = 125 °C	-	2	500	μA
I _{EBO}	emitter-base cut-off current (collector open)	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{lead} = 25 ^{\circ}\text{C}$	-	0.05	100	μA
V _{CEsat}	collector-emitter saturation voltage	$I_C = 0.75 \text{ A}$; $I_B = 0.15 \text{ A}$; $T_{lead} = 25 ^{\circ}\text{C}$; Fig. 3	-	0.24	1	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 0.75 \text{ A}$; $I_B = 0.15 \text{ A}$; $T_{lead} = 25 ^{\circ}\text{C}$; Fig. 4	-	0.93	1.3	V
h _{FE}	DC current gain	I_C = 10 mA; V_{CE} = 5 V; T_{lead} = 25 °C; Fig. 5; Fig. 6	12	22	32	
		I_C = 100 mA; V_{CE} = 5 V; T_{lead} = 25 °C; Fig. 5; Fig. 6	14	24	34	
		$I_C = 0.75 \text{ A}; V_{CE} = 5 \text{ V}; T_{lead} = 25 ^{\circ}\text{C};$ Fig. 5; Fig. 6	12	15.5	20	
Dynamic ch	naracteristics (resistive loa	d)				
t _s	storage time	I _C = 1 A; I _{Bon} = 0.2 A; I _{Boff} = -0.2 A;	-	2	-	μs
t _f	fall time	$R_L = 75 \Omega$; $V_{BB} = -4 V$; $T_{lead} = 25 °C$; Fig. 7; Fig. 8	-	320	-	ns





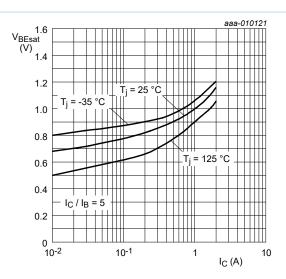


Fig. 4. Base-emitter saturation voltage as a function of collector current; typical values

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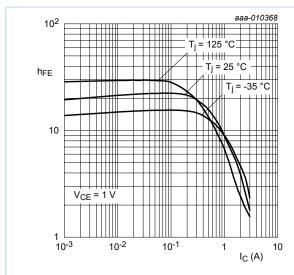


Fig. 5. DC current gain as a function of collector current; typical values

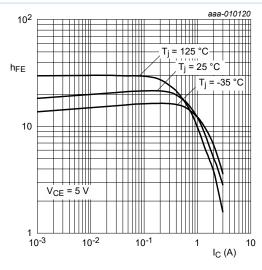


Fig. 6. DC current gain as a function of collector current; typical values

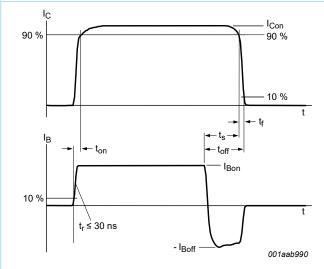
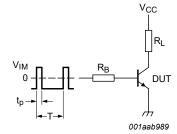


Fig. 7. Switching times waveforms for resistive load

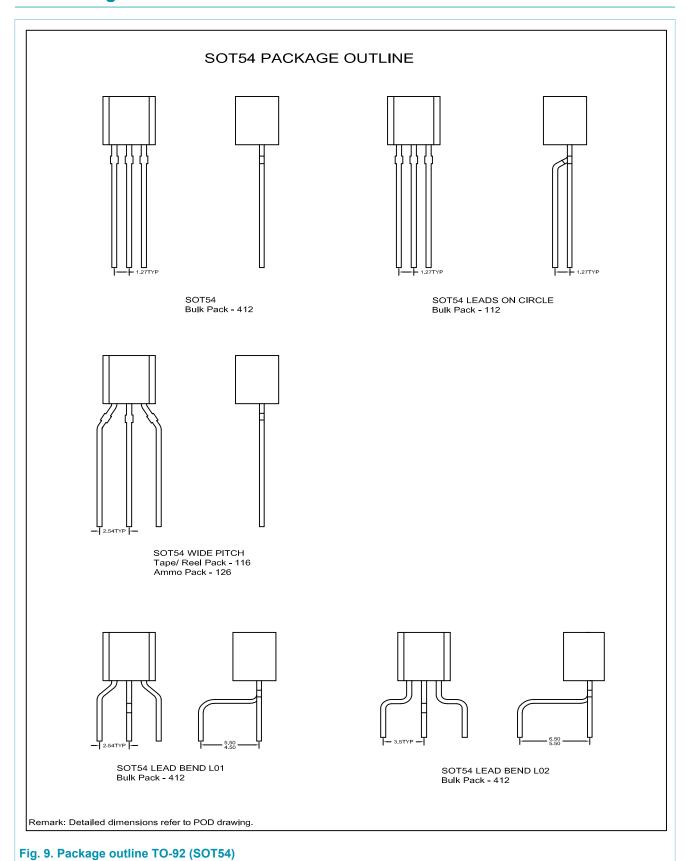


 V_{IM} = -6 to +8 V; V_{CC} = 250 V; t_p = 20 μ s; δ = $\frac{t_p}{T}$ = 0.01 R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig. 8. Test circuit for resistive load switching

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10. Package outline



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11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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